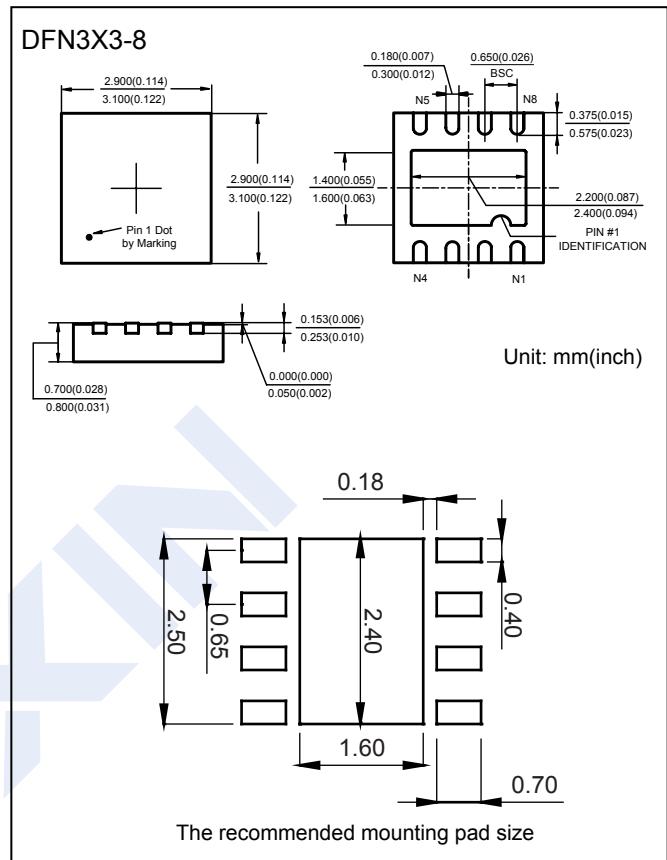
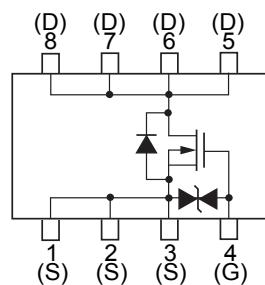


## N-Channel MOSFET

### FK8V03050

#### ■ Features

- $V_{DS}$  (V) = 33V
- $I_D$  = 8 A ( $V_{GS}$  = 10V)
- $R_{DS(ON)} < 15\text{m}\Omega$  ( $V_{GS}$  = 10V)
- $R_{DS(ON)} < 25\text{m}\Omega$  ( $V_{GS}$  = 4.5V)
- High-speed switching :  $Q_g = 5.1\text{nC}$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	33	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	8	A
		10	
Pulsed Drain Current	$I_{DM}$	32	
Power Dissipation	$P_D$	1	W
		1.5	
Junction Temperature	$T_J$	150	
Operating Ambient Temperature	$T_{opr}$	-40 to 85	
Storage Temperature Range	$T_{stg}$	-55 to 150	

## N-Channel MOSFET

### FK8V03050

■ Electrical Characteristics Ta = 25°C

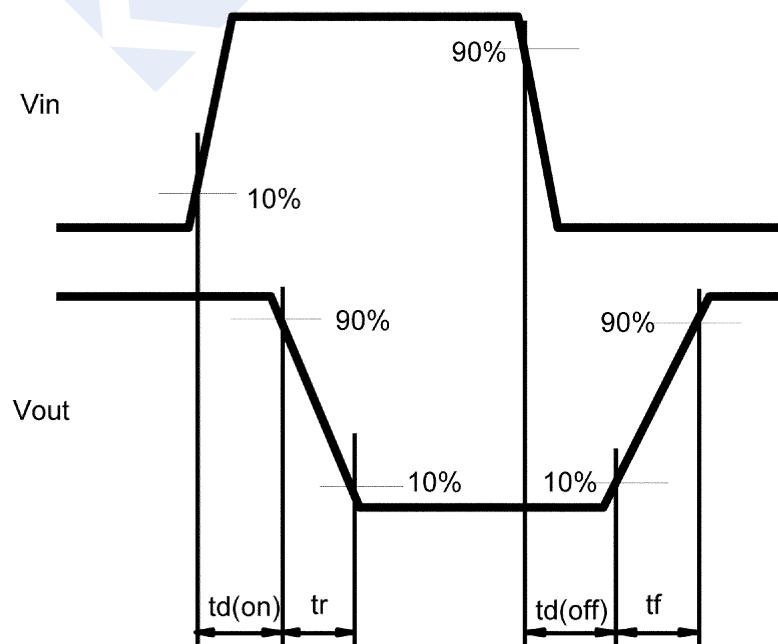
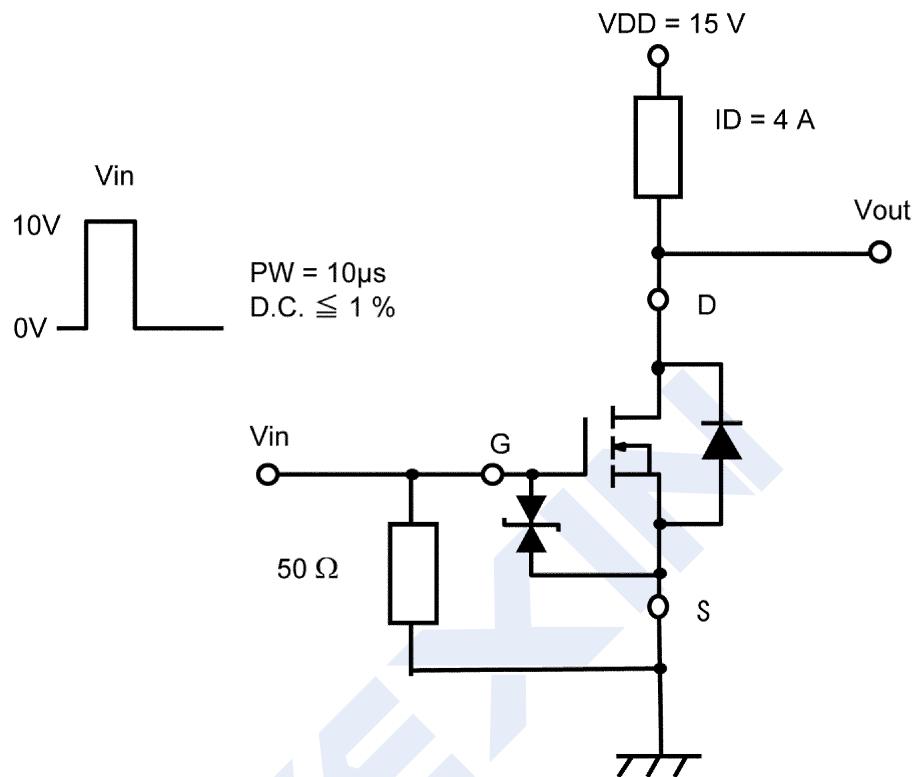
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =1 mA, V <sub>GS</sub> =0V	33			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>D</sub> =33V, V <sub>GS</sub> =0V			10	uA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>D</sub> =0V, V <sub>GS</sub> =±16V			± 10	uA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>D</sub> =10V, I <sub>D</sub> =0.73mA	1		2.5	V
Static Drain-Source On-Resistance	R <sub>D(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =4A			15	m Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A			25	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>D</sub> =10V, f=1MHz		520		pF
Output Capacitance	C <sub>oss</sub>			110		
Reverse Transfer Capacitance	C <sub>rss</sub>			70		
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =0 to 4.5V, V <sub>D</sub> =15V, I <sub>D</sub> =8A		5.1		nC
Gate Source Charge	Q <sub>gs</sub>			1.8		
Gate Drain Charge	Q <sub>gd</sub>			2.3		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS</sub> =0 to 10V, V <sub>D</sub> =15V, I <sub>D</sub> =4A		8		ns
Turn-On Rise Time	t <sub>r</sub>			4		
Turn-Off DelayTime	t <sub>d(off)</sub>	V <sub>GS</sub> =10 to 0 V, V <sub>D</sub> =15V, I <sub>D</sub> =4A		32		
Turn-Off Fall Time	t <sub>f</sub>			10		
Maximum Body-Diode Continuous Current	I <sub>S</sub>	I <sub>S</sub> =4A, V <sub>GS</sub> =0V			8	A
Diode Forward Voltage	V <sub>SD</sub>				1.2	V

■ Marking

Marking	3E
---------	----

**N-Channel MOSFET****FK8V03050**

## ■ Typical Characteristics

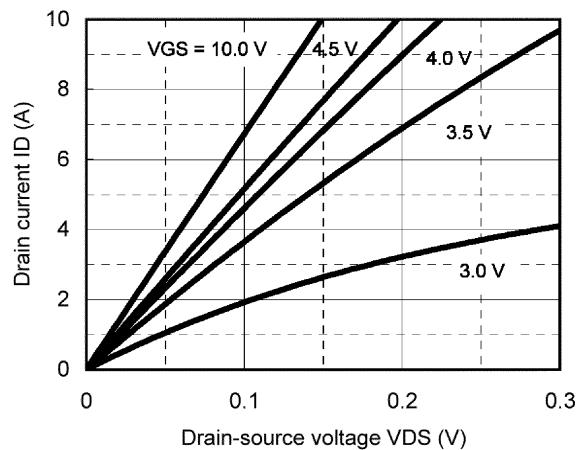


## N-Channel MOSFET

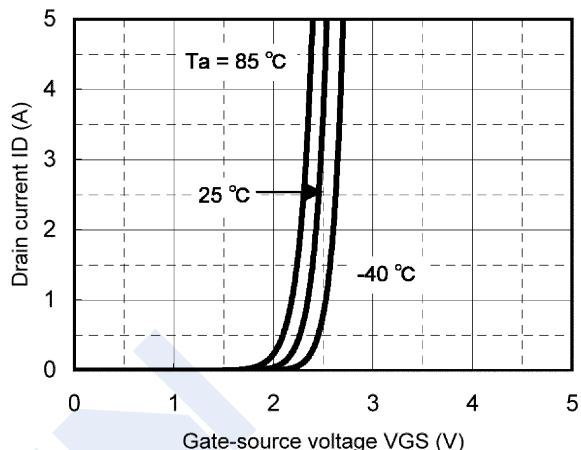
FK8V03050

## ■ Typical Characteristics

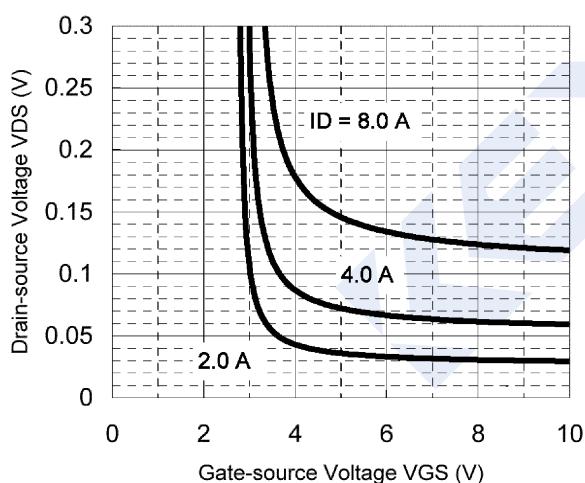
ID - VDS



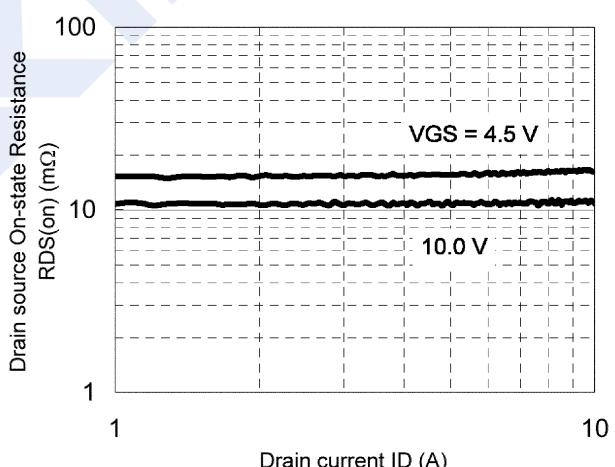
ID - VGS



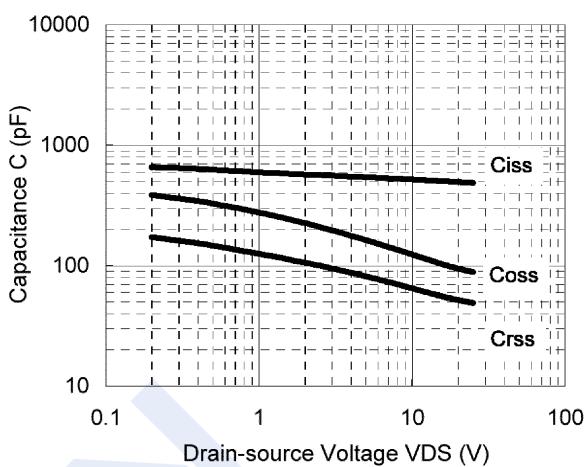
VDS - VGS



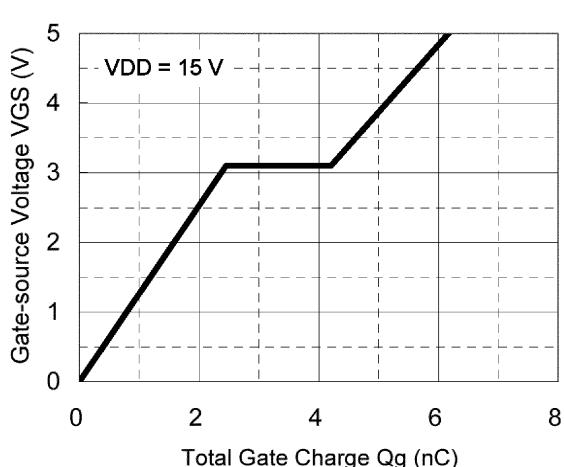
RDS(on) - ID



Capacitance - VDS



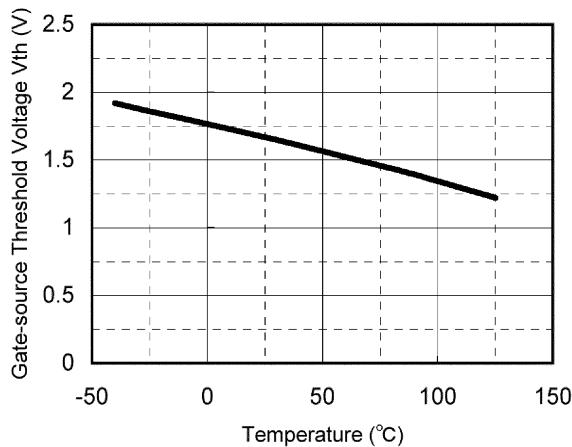
Dynamic Input/Output Characteristics



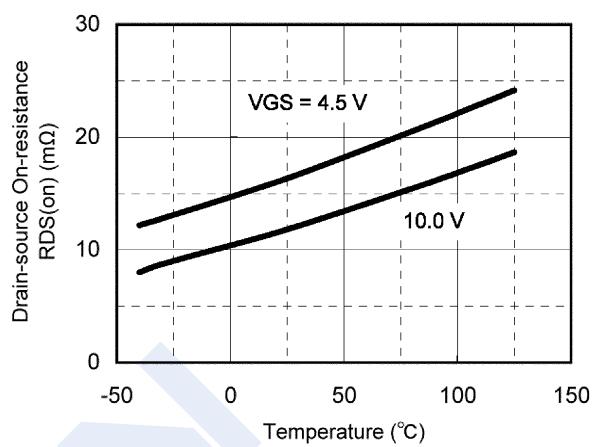
## N-Channel MOSFET

### FK8V03050

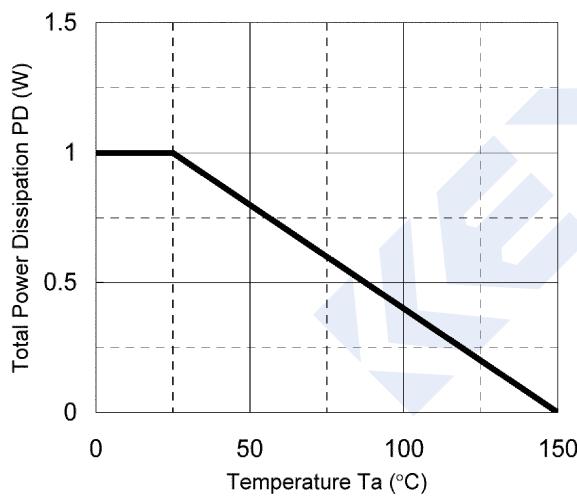
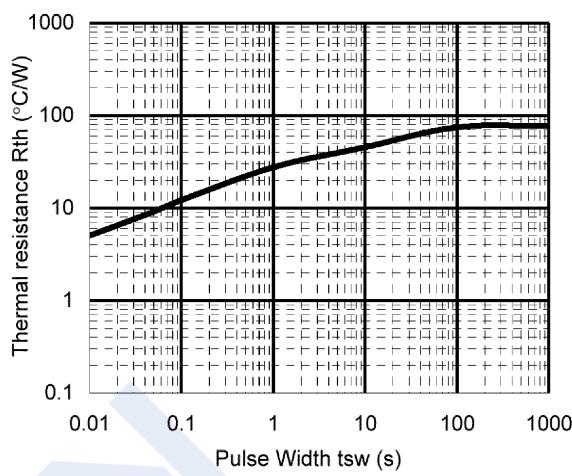
#### ■ Typical Characteristics

V<sub>th</sub> - Ta

RDS(on) - Ta



PD - Ta

R<sub>th</sub> - tsw

Safe Operating Area

